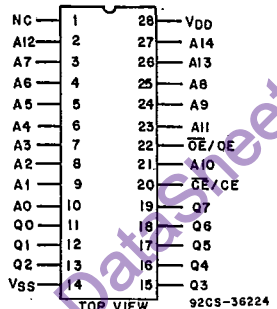
CDM53256



TERMINAL ASSIGNMENT

CMOS 32,768-Word by 8-Bit LSI Static ROM

Features:

- *Asynchronous operation*
- *Fast access time - 250 ns max.*
- *Low standby and operating power -*
  I_{SBY2} = 2 μA typical
  I_{OPER2} = 12 mA max. at t_{cyc} = 1 μs
  = 36 mA max. at t_{cyc} = 250 ns
- *Automatic power down*
- *Mask-programmable chip enable and output enable*
- *TTL input and output compatible*
- *28-pin JEDEC standard pin out: Pin compatible with the 27256 EPROM*

The RCA-CDM53256 is a 262,144-bit asynchronous mask-programmble, CMOS READ-ONLY memory organized as 32,768 eight-bit words. The CDM53256 is designed to be used with a wide range of general-purpose microprocessor systems, including the RCA CDP1800 series system. One chip enable input and an output enable function are provided for memory expansion and output buffer control. Chip enable (CE) gates the address and output buffers and powers down the chip to the standby mode. The output enable (OE) controls the output buffers to eliminate bus contention. The polarities of the chip enable and the output enable are user mask-programmble.

The CDM53256 is supplied in 28-lead, hermetic, dual-in-line side-brazed ceramic (D suffix), in 28-lead dual-in-line plastic (E suffix) and in 28-lead small-outline (SO) plastic (M suffix) packages.

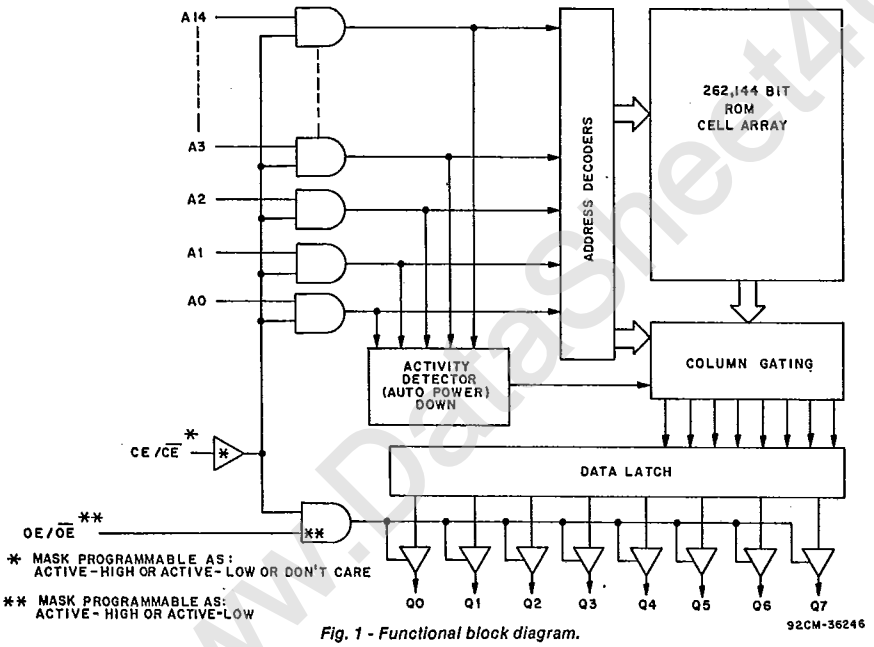


Fig. 1 - Functional block diagram.

File Number **1453**

CDM53256

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MAXIMUM RATINGS, *Absolute-Maximum Values:*

DC SUPPLY-VOLTAGE RANGE, (V_{DD})
(Voltage referenced to V_{SS} terminal) ..... -0.5 to +7V
INPUT VOLTAGE RANGE, ALL INPUTS ..... -0.5 to V_{DD} +0.5 V
DC INPUT CURRENT, ANY ONE INPUT ..... ±10 mA
POWER DISSIPATION PER PACKAGE (P_D):
For T_A = -40 to +60°C (PACKAGE TYPE E) ..... 500 mW
For T_A = +60 to +85°C (PACKAGE TYPE E) ..... Derate Linearly at 8 mW/°C to 300 mW
For T_A = -55 to +100°C (PACKAGE TYPE D) ..... 500 mW
For T_A = +100 to +125°C (PACKAGE TYPE D) ..... Derate Linearly at 8 mW/°C to 300 mW
For T_A = -40 to +85°C (PACKAGE TYPE M)* ..... 425 mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR
For T_A = FULL PACKAGE-TEMPERATURE RANGE (All Package Types) ..... 100 mW
OPERATING-TEMPERATURE RANGE (T_A):
PACKAGE TYPE D ..... -55 to +125°C
PACKAGE TYPE E and M ..... -40 to +85°C
STORAGE-TEMPERATURE RANGE (T_{stg}) ..... -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s maximum ..... +265°C

*Printed-circuit board mount: 57 mm x 57 mm minimum area x 1.6 mm thick G10 epoxy glass, or equivalent.

RECOMMENDED OPERATING CONDITIONS at T_A = -40 to +85°C

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	Min.	Max.	
DC Operating Voltage Range	4	6	V
Input Voltage Range	V_{SS}	V_{DD}	

STATIC ELECTRICAL CHARACTERISTICS at T_A = -40 to +85°C, V_{DD} = 5 V ± 10%, Except as noted

CHARACTERISTIC		CONDITIONS	LIMITS ALL TYPES			UNITS
			Min.	Typ.*	Max.	
Average Operating Device Current[a]	I_{OPER1}[d]	V_{IN} = V_{IL}, V_{IH}; CE = V_{IH}; ($\overline{CE}$ = V_{IL}) t_{cyc} = 1 µs	—	—	16	mA
		t_{cyc} = 250 ns	—	—	40	
	I_{OPER2}[e]	V_{IN} = 0.2 V, V_{DD} -0.2 V; $\overline{CE}$ = V_{DD} -0.2 V; ($\overline{CE}$ = 0.2 V) t_{cyc} = 1 µs	—	—	12	
		t_{cyc} = 250 ns	—	—	36	
DC Active Device Current[b]	I_{ACT1}[d]	V_{IN} = V_{IL}, V_{IH}; CE = V_{IH}; ($\overline{CE}$ = VIL)	—	—	15	mA
	I_{ACT2}[e]	V_{IN} = 0.2 V, V_{DD} -0.2 V; $\overline{CE}$ = V_{DD} -0.2 V; ($\overline{CE}$ = 0.2 V)	—	—	50	µA
Standby Device Current[c]	I_{SBY1}[d]	V_{IN} = V_{IL}, V_{IH}; CE = V_{IL}; ($\overline{CE}$ = V_{IH})	—	—	1.5	mA
	I_{SBY2}[e]	V_{IN} = 0.2 V, V_{DD} -0.2 V; $\overline{CE}$ = 0.2 V; ($\overline{CE}$ = V_{DD} -0.2 V)	—	2	50	µA
Output Voltage Low-Level	V_{OL}	I_{OL} = 3.2 mA	—	—	0.4	V
Output Voltage High-Level	V_{OH}	I_{OH} = -3.2 mA	2.4	—	—	
Input Low Voltage	V_{IL}	—	—	—	0.8	
Input High Voltage	V_{IH}	—	2.2	—	—	
Input Leakage Current (Any Input)	I_{IN}	$V_{SS} \leq V_{IN} \leq V_{DD}$	—	—	±1	µA
3-State Output Leakage Current	I_{OUT}	$V_{SS} \leq V_{OUT} \leq V_{DD}$	—	—	±1	
Input Capacitance	C_{IN}	f = 1 MHz, T_A = 25°C	—	5	10	pF
Output Capacitance	C_{OUT}	f = 1 MHz, T_A = 25°C	—	6	12	

*Typical values are for T_A = 25° C and nominal V_{DD}.
[a]Address inputs toggling, chip enabled, outputs open circuit.
[b]Inputs stable, chip enabled, outputs open circuit.
[c]Independent of address input activity, chip disabled.
[d]TTL inputs.
[e]CMOS inputs.

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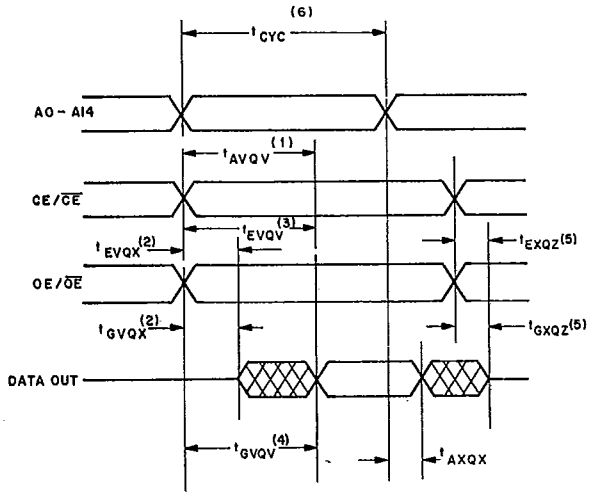
DYNAMIC ELECTRICAL CHARACTERISTICS at T_A = -40 to +85°C, V_{DD} = 5 V ± 10%, Input t_r, t_f = 10 ns; C_L = 100 pF, and 1 TTL Load; Input Pulse Levels: 0.8 V to 2.2 V

CHARACTERISTICS		LIMITS		UNITS
		Min.	Max.	
Address access time	t_{AVQV}	—	250	ns
Chip enable to output active	t_{EVQX}	0	—	
Output enable to output active	t_{GVQX}	0	—	
Chip enable access	t_{EVQV}	—	250	
Output enable to output valid	t_{GVQV}	—	90	
Data hold after address	t_{AXQX}	10	—	
Chip disable to output high Z	t_{EXQZ}	—	90	
Output disable to output high Z	t_{GXQZ}	—	70	
Cycle time	t_{CYC}	250	—	



NOTES:
(1) Assumes t_{GVQV} & t_{EVQV} are satisfied.
(2) Output Active requires both Chip Enable & Output Enable Active.
(3) Assumes t_{AVQV} & t_{GVQV} are satisfied.
(4) Assumes t_{AVQV} & t_{EVQV} are satisfied.
(5) Either invalid Chip Enable or Output Enable causes Output High Z
(6) Generates 10 ns Valid Output Pulses (i.e., t_{CYC}-t_{AVQV}+t_{AXQX})

NOTE: TIMING MEASUREMENT REFERENCE LEVEL IS 1.5 V.

92CM-36238

Fig. 2 - Timing waveforms.

APPLICATION INFORMATION

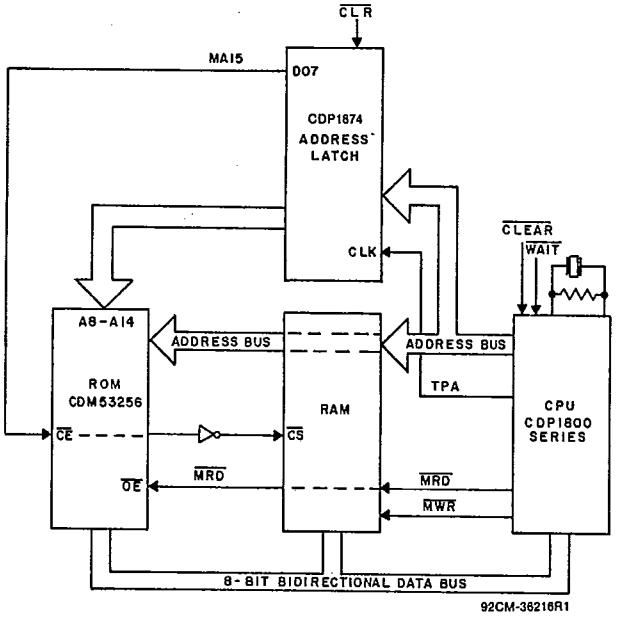


Fig. 3 - Typical CDP1800 series microprocessor system.

Decoupling Capacitors

The CDM53256 operates with a low average dc power supply current that varies with cycle time. However, CDM53256 is a large ROM with many internal nodes. Precharging of selected nodes during portions of the memory cycle results in short duration peak currents that can be much higher than the average dc value. The rise and fall times of the peak current pulses can have a value sufficient to generate unwanted system noise components. To minimize or eliminate the effects of the current spikes, a 0.1 μF ceramic decoupling capacitor is recommended between the V_{DD} and V_{SS} pins of every ROM device.